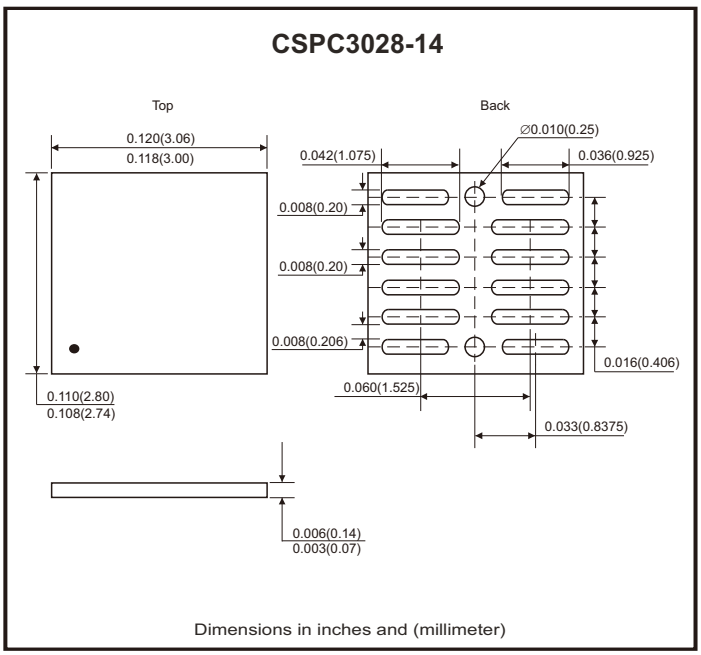
CMSBN12209-HF

Dual N-Channel
RoHS Device
Halogen Free

Features

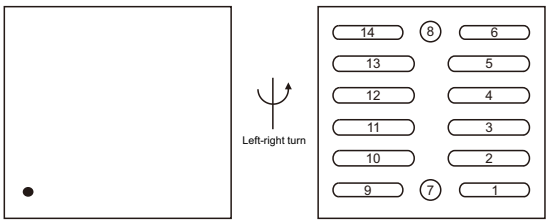
- It is ESD protected.
- This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.



Mechanical data

- Case: CSPC3028-14, standard package, molded plastic.

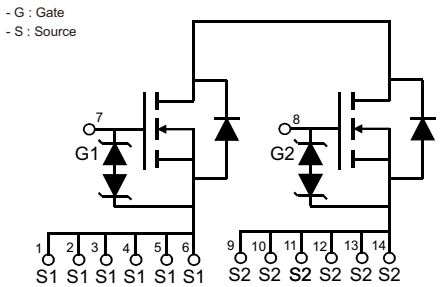
Pin assignment



Top View
- Solid dot : Pin 1

Bottom View
- Pin 1, 2, 3, 4, 5, 6 : Source 1
- Pin 9, 10, 11, 12, 13, 14 : Source 2
- Pin 7 : Gate 1
- Pin 8 : Gate 2

Circuit diagram



Maximum Ratings (at T_A=25°C unless otherwise noted)

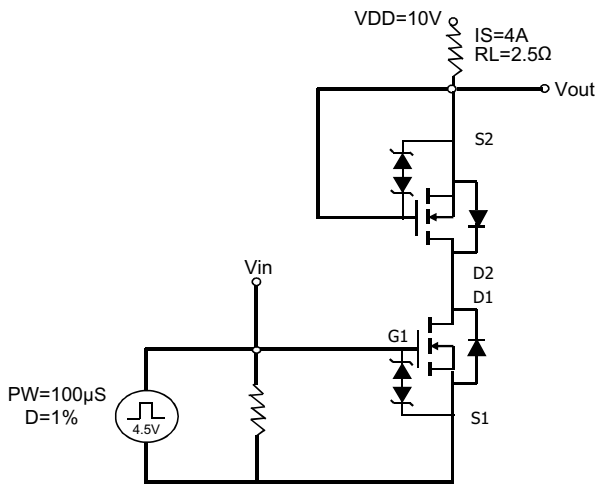
Parameter	Symbol	Value	Unit
Source to source voltage	V_{SSS}	12	V
Gate-source voltage	V_{GSS}	±8	V
Source current DC (Note 1)	I_S	19.8	A
Source current pulse (Note 1, 2)	I_{SP}	198	A
Total dissipation (Note 1)	P_T	3.1	W
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{STG}	-55 to +150	

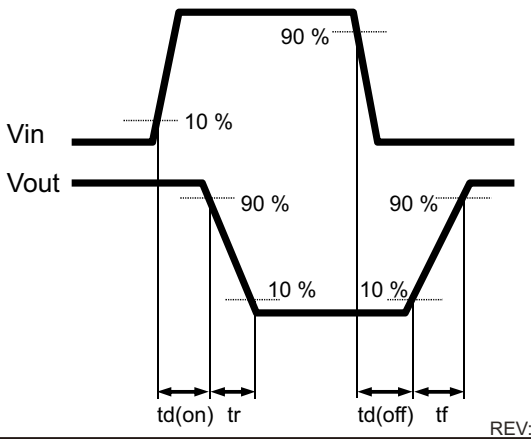
Notes: 1. Mounted on FR4 board (25.4mm x 25.4mm x t1.0mm) using the minimum recommended pad size (36μm copper).
2. t = 10ms, duty cycle = 1 %

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static parameters						
Source to source breakdown voltage	BV_{SSS}	I_S = 1mA, V_{GS} = 0V	12			V
Zero-gate voltage source current	I_{SSS}	V_{SS} = 10V, V_{GS} = 0V			1	μA
Gate to source leakage current	I_{GSS}	V_{SS} = 0V, V_{GS} = ±8V			±10	μA
Gate to source threshold voltage	V_{TH}	V_{S2S1} = 6V, I_{S1} = 2.3mA	0.35	0.77	1.4	V
		V_{S1S2} = 6V, I_{S2} = 2.3mA				
Source to source on-state resistance	$R_{SS(on)}$	V_{GS} = 4.5V, I_S = 3A	0.8	1.2	1.56	mΩ
		V_{GS} = 3.8V, I_S = 3A	0.9	1.3	1.69	
		V_{GS} = 3.1V, I_S = 3A	1.0	1.4	1.82	
		V_{GS} = 2.5V, I_S = 3A	1.1	1.6	3.20	
Input capacitance	C_{iss}	V_{SS} = 10V, V_{GS} = 0V, f = 1kHz		6315		pF
Output capacitance	C_{oss}			1393		
Reverse transfer capacitance	C_{rss}			1106		
Turn-on delay time (Note 3)	$t_{d(on)}$	V_{DD} = 10V, I_S = 4A, V_{GS} = 4.5V		1.2		μS
Turn-on rise time (Note 3)	t_r			5.7		
Turn-off delay time (Note 3)	$t_{d(off)}$			11		
Turn-off fall time (Note 3)	t_f			15.4		
Total gate charge (Note 3)	Q_g	V_{SS} = 10V, I_S = 10A, V_{GS} = 4.5V		75		nC
Gate1-source1 charge (Note 3)	Q_{g1s1}			15		
Gate1-source2 charge (Note 3)	Q_{g1s2}			36		
Diode forward voltage	$V_{F(S-S)}$	V_{G1S1} = 0V, V_{G2S2} = 4.5V, I_S = 3A			1.0	V
		V_{G1S1} = 4.5V, V_{G2S2} = 0V, I_S = 3A				

Notes: 3. When FET1 is measured,G2 and S2 are short-circuited.





Rating and Characteristic Curves (CMSBN12209-HF)

Fig.1 - I_S — V_{SS}

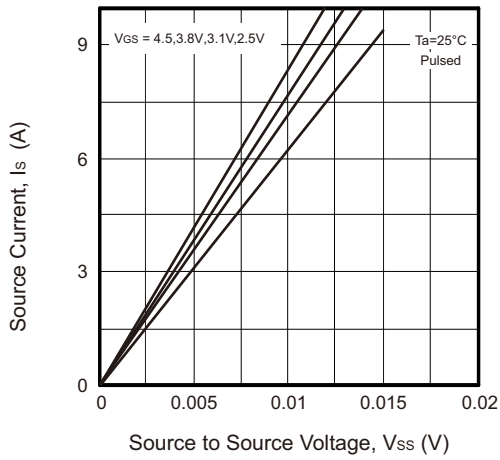


Fig.2 - I_S — V_{GS}

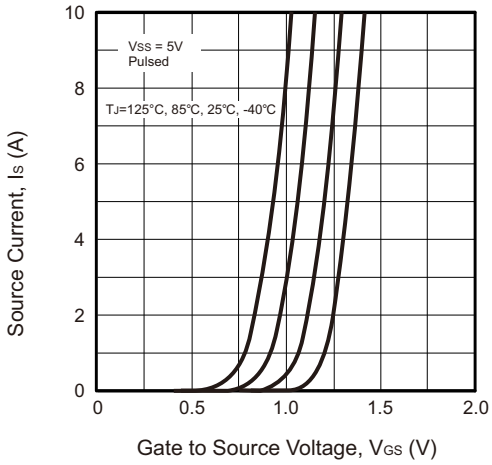


Fig.3 - $R_{SS(on)}$ — I_S

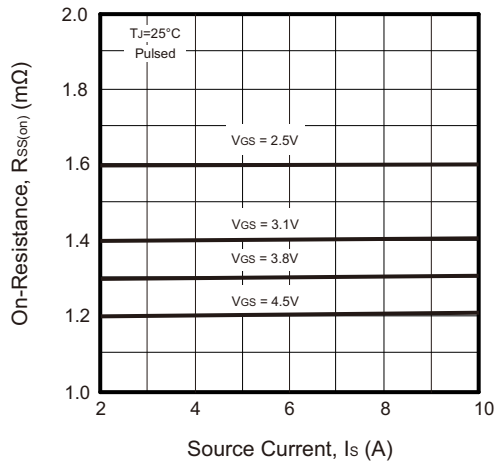


Fig.4 - $R_{SS(on)}$ — V_{GS}

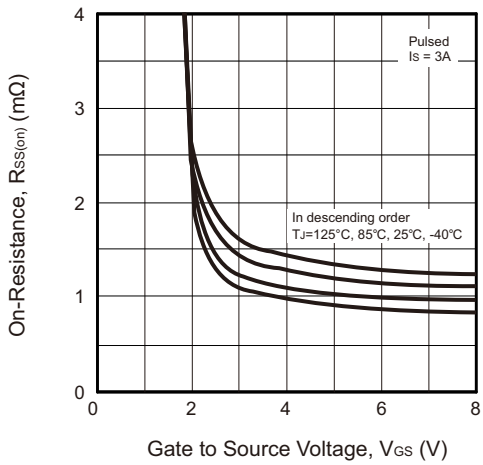


Fig.5 - I_F — V_F

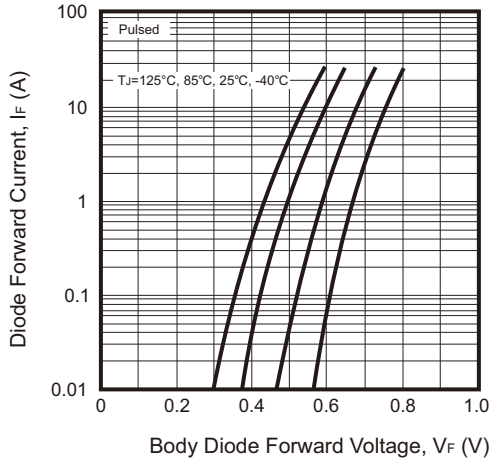
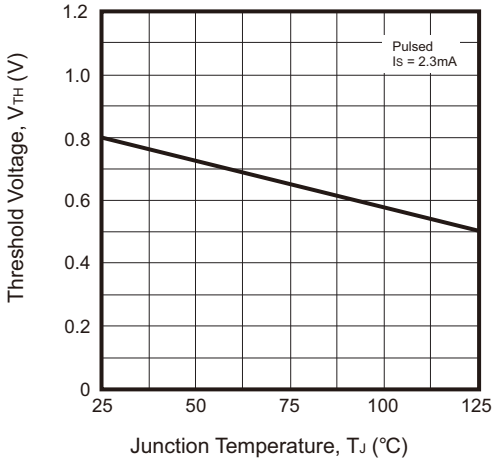


Fig.8 - Threshold Voltage



Rating and Characteristic Curves (CMSBN12209-HF)

Fig.7 - Capacitance

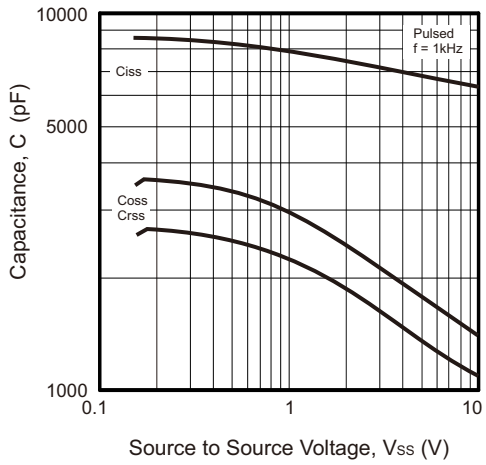


Fig.8 - Gate Charge

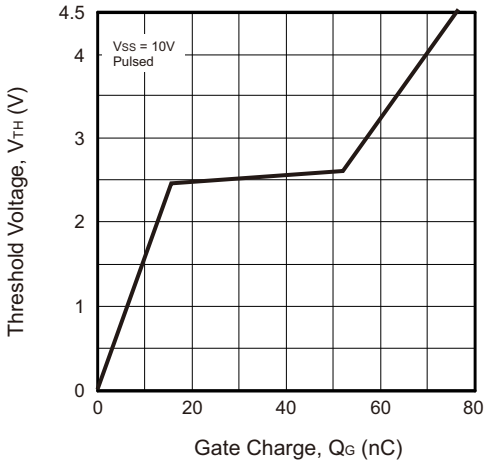


Fig.9 - Normalized Traisient Thermal Impendance

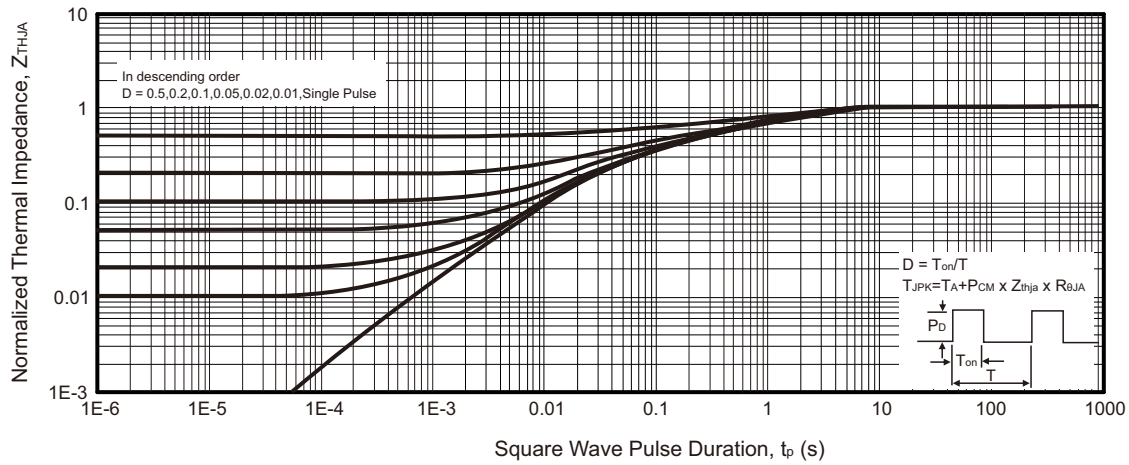


Fig.10 - Maximum Forward Biased Safe Operating Area